

AMENDMENT TO THE CLAIMS

1-9. (cancelled)

10. (original) An integrated interconnect assembly for a microstructure comprising:

a microstructure body including a microstructure cavity having a bond pad formed on an inner wall of the microstructure cavity and conductively coupled to a lead on the microstructure body.

11. (currently amended) The assembly of claim 10 and further comprising a nested ~~microstructure~~ body supportable in the ~~microstructure~~ microstructure cavity and having a bond pad interfaceable with the bond pad formed on the inner wall of the microstructure cavity.

12. (original) In combination:

a first body having a bond pad formed thereon and a second body having a nest cavity and the first body supported in the nest cavity; and

means for electrically coupling the bond pad on the first body supported in the nest cavity to circuitry coupled to the second body.

13. (original) The combination of claim 12 wherein the means for electrically coupling includes a raised bond pad formed on a wall of the nest cavity of the second body.

14. (original) The combination of claim 12 wherein the first body is a slider having a transducer electrically coupled to the bond pad on the first body.

15-20. (Cancelled)

21. (new) The assembly of claim 11 wherein the nested body is a slider having a transducer electrically coupled to the bond pad on the slider.

22. (new) The assembly of claim 10 wherein the microstructure body includes a base portion and a floating portion floatable coupled to the base portion and the microstructure cavity is formed in the floating portion.

23. (new) The assembly of claim 22 wherein the floating portion forms a microactuatable microstructure.

24. (new) The assembly of claim 10 wherein the bond pad is raised from a surface of the inner wall of the microstructure cavity.

25. (new) The assembly of claim 10 wherein the microstructure body is formed of a silicon substrate.

26. (new) The assembly of claim 10 wherein the bond pad on the inner wall of the microstructure cavity and the lead are formed in a trench etched in the microstructure body.

27. (new) The assembly of claim 10 wherein the microstructure is etched to form the microstructure cavity and the bond pad along the inner wall of the microstructure cavity.

28. (new) The assembly of claim 10 including a plurality of bond pads along the inner wall of the microstructure cavity.

29. (new) The assembly of claim 10 and further comprising at least four bond pads along the inner wall of the microstructure cavity.

30. (new) An interconnect for circuit leads on a microstructure comprising:

at least one bond pad formed on an etched surface of an interior cavity of the microstructure.

31. (new) The interconnect of claim 30 including a plurality of bond pads formed on the etched surface of the interior cavity of the microstructure.

32. (new) The interconnect of claim 30 wherein the at least one bond pad includes a raised surface spaced from the etched surface of the interior cavity.

33. (new) The interconnect of claim 30 wherein the microstructure forms a MEMS actuator for a slider of a data storage device.

34. (new) The interconnect of claim 33 wherein the MEMS actuator includes a base portion and a floating portion and the etched surface having the at least one bond pad formed thereon is formed on the floating portion to interface with a bond pad on the slider.

35. (new) The interconnect of claim 30 including a slider disposed in the interior cavity of the microstructure having a bond pad adapted to electrically interface with the at least one bond pad on the etched surface of the interior cavity of the microstructure.